

Silicon NPN transistor in a TO-92 Plastic Package.

$V_{CEO} < 80V. (I_C = 1mA).$

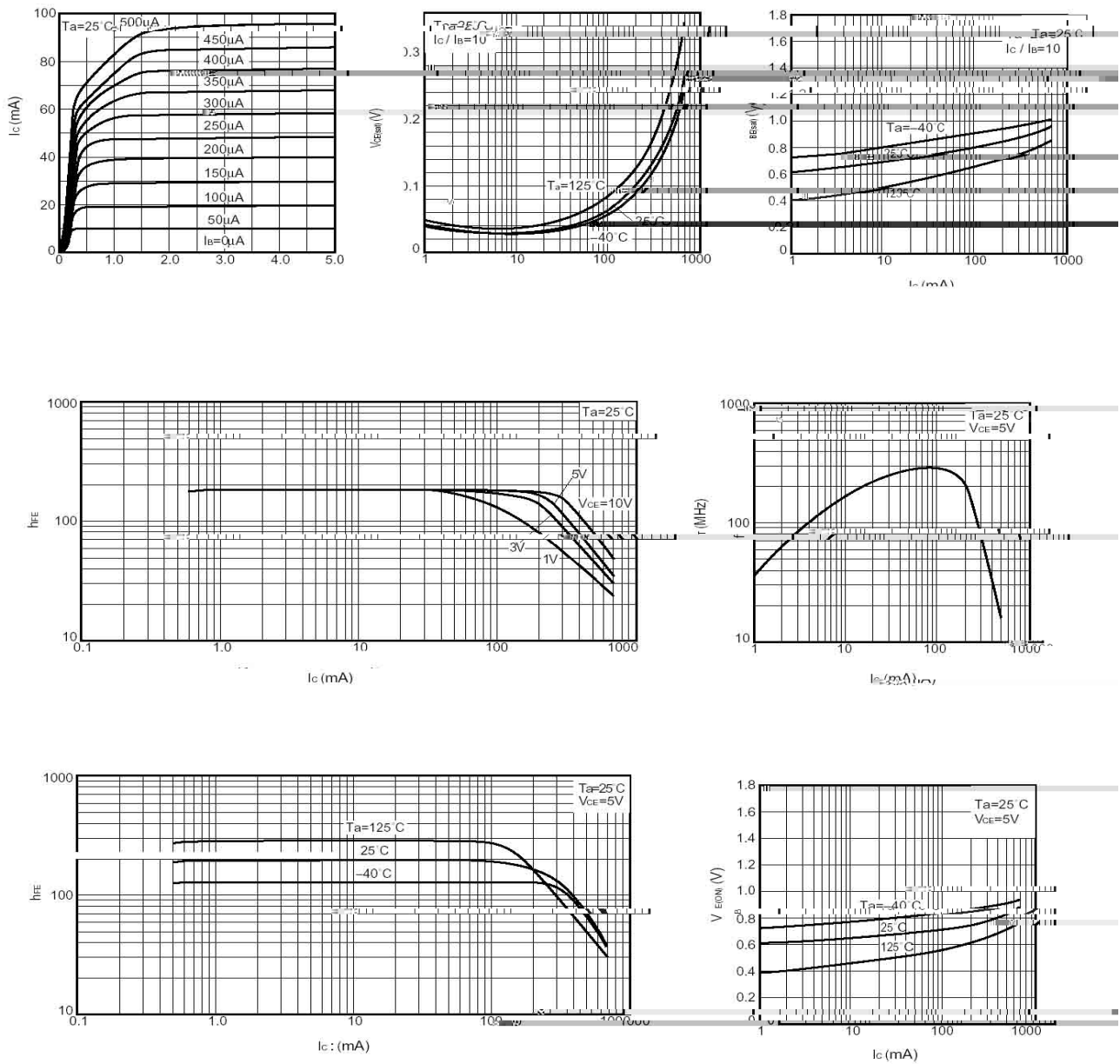
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	500	mA
Peak Collector Current	I_{CM}	1	A
Peak Base Current	I_{BM}	200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=80V$ $I_E=0$			0.05	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5$ $I_C=0$			0.05	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1V$ $I_C=100mA$	100			
	$h_{FE(2)}$	$V_{CE}=1V$ $I_C=10mA$	100			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$			0.25	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=1V$ $I_C=100mA$			1.2	V
Transition Frequency	f_T	$V_{CE}=2V$ $I_C=10mA$ $f=100MHz$	100			MHz

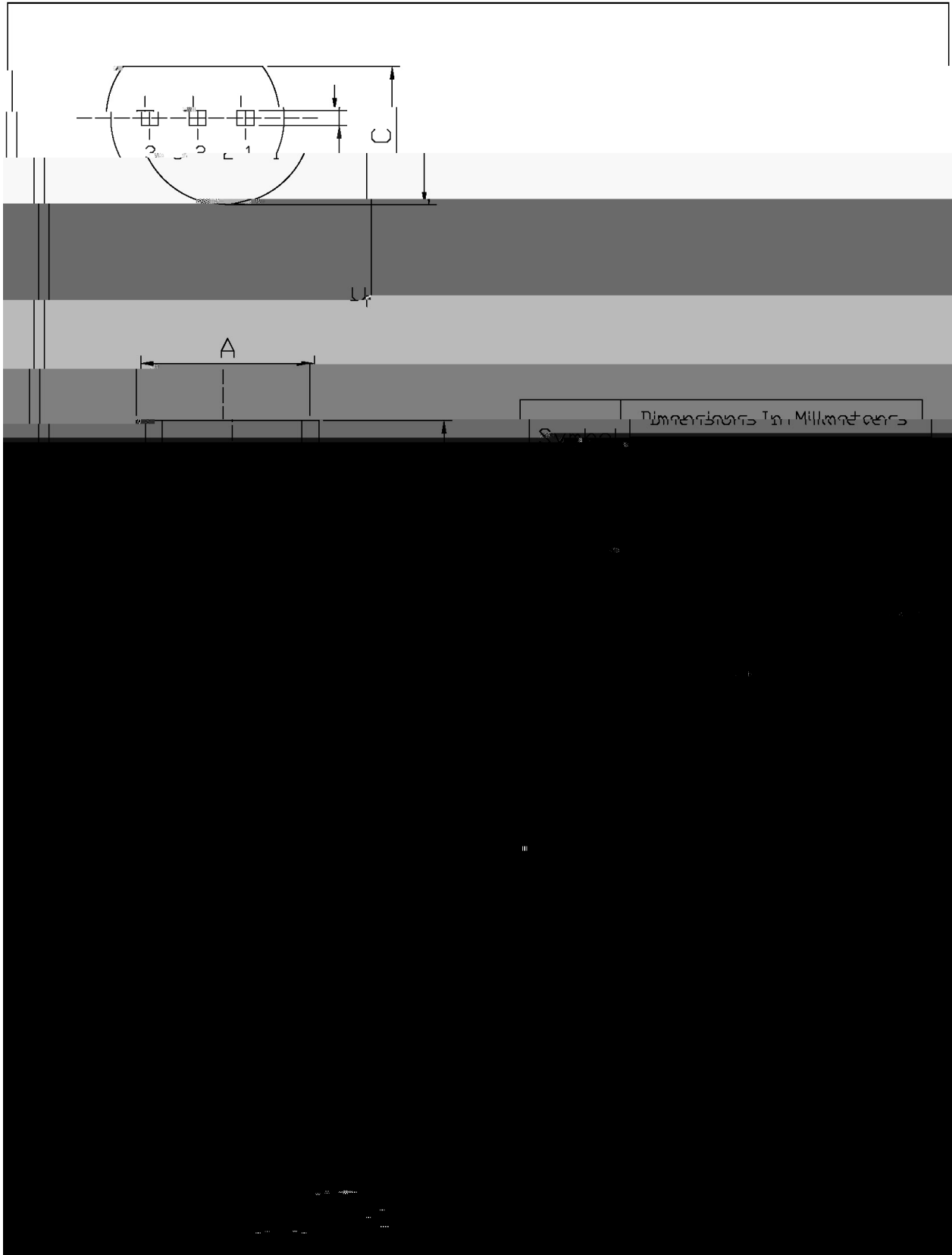
/ Electrical Characteristic Curve



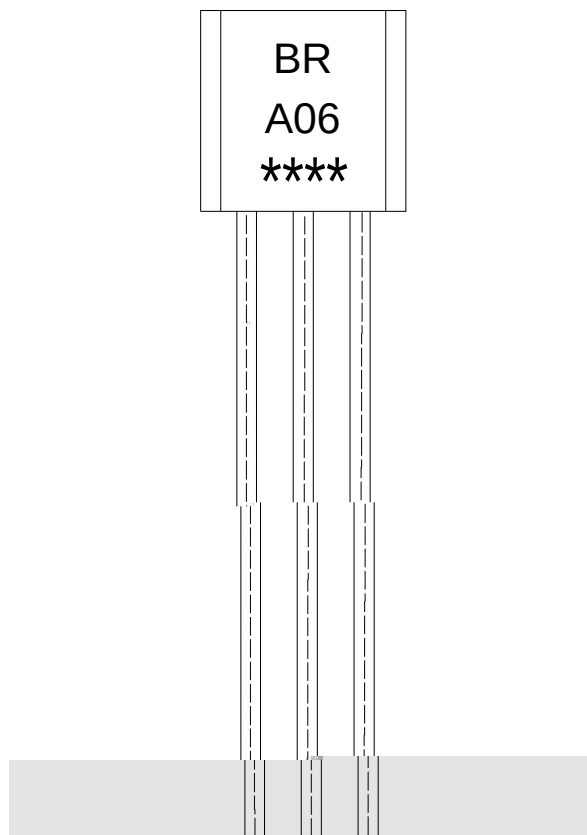
/ Package Dimensions

T0-92

Unit: mm



/ Marking Instructions



Note:

BR: Company Code.

A06: Product Type.

****: Lot No. Code,code change with Lot No.

